



Future Normal in Semiconductor

2025년 2월 14일(금), 15:10-17:10

Room L(하트II+III), 6층

B. Patterning (Lithography & Etch Technology) 분과

078_[FL3-B] Etch

좌장: 채희엽 교수(성균관대학교), 이상헌 교수(이화여자대학교)

<p>초청 FL3-B-1 15:10-15:40</p>	<p>Semiconductor Equipment Technology: What's Next? Dougyoung Sung Mechatronics Research, Samsung Electronics Co., Ltd.</p>
<p>FL3-B-2 15:40-15:55</p>	<p>Low-temperature SiO₂ Contact Hole Etching Using C₄F₈ Plasmas 유상현^{1,2}, 김창구^{1,2} ¹Department of Chemical Engineering, Ajou University, ²Department of Energy Systems Research, Ajou University</p>
<p>FL3-B-3 15:55-16:10</p>	<p>High-throughput Isotropic Atomic Layer Etching of Hafnia Films Using F Radicals and Al Precursors Gyejun Cho, Jehwan Hong, Hye-Lee Kim, and Won-Jun Lee Department of Nanotechnology and Advanced Materials Engineering, Sejong University</p>
<p>초청 FL3-B-4 16:10-16:40</p>	<p>Technical Challenge and Development of HARC Etching Sang Wook Park, Jae Won Lee, Sang Heon Song, Kyung Tae Kim, Ki Jun Yun, Hoo Woong Lee, Woo June Kwon, Chung Won Seo, and Hyun Min Lee SK hynix Inc.</p>
<p>FL3-B-5 16:40-16:55</p>	<p>Investigation on the Effect of Tailored Waveform Bias on the Formation of SiO₂/Si Trench Etch Profile in SF₆/O₂/Ar Plasma Taejun Park¹, Jihoon Park¹, Ingyu Lee¹, Namkyun Kim², and Gon-Ho Kim¹ ¹Seoul National University, ²Samsung Electronics Co., Ltd.</p>
<p>FL3-B-6 16:55-17:10</p>	<p>Ultrathin Ni Catalyst for CMOS-compatible Metal-assisted Chemical Etching of Si Kyunghwan Kim^{1,2}, Haekyun Bong^{1,3}, and Jungwoo Oh^{1,3} ¹School of Integrated Technology, Yonsei University, ²Center for Quantum Technology, KIST, ³BK21 Graduate Program in Intelligent Semiconductor Technology, Yonsei University</p>